Product data sheet

1. General description

Hyperfast power diode in a SOD113A (2-lead TO-220F) plastic package.

2. Features and benefits

- · Low reverse recovery current
- Low thermal resistance
- Low leakage current
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			6	000		V
I _{F(AV)}	average forward current	$δ = 0.5$; square-wave pulse; $T_h \le 97$ °C; Fig. 1; Fig. 2; Fig. 3	5		А		
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_h \le$ 97 °C; square-wave pulse	10			А	
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	60		А		
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	65		А		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V_{F}	forward voltage	I _F = 5 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.35	2.1	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	11	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	Α	anode		K — ↓ A 001aaa020
mb	n.c.	mounting base; isolated		001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYC5X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220F "full pack"	SOD113A		

7. Marking

Table 4. Marking codes

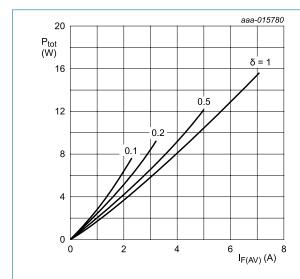
Type number	Marking codes
BYC5X-600P	BYC5X-600P

8. Limiting values

Table 5. Limiting values

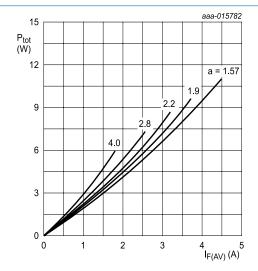
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	$δ$ = 0.5; square-wave pulse; $T_h \le 97$ °C; Fig. 1; Fig. 2; Fig. 3	5	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _h ≤ 97 °C; square-wave pulse	10	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	60	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	65	А
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.801 \text{ V; } R_{\text{s}} = 0.062 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

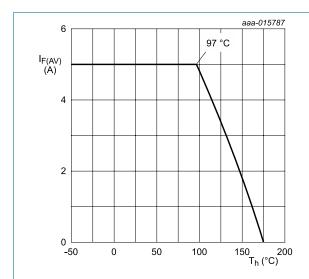


a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.801 V; R_s = 0.062 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

WeEn Semiconductors BYC5X-600P

Hyperfast power diode





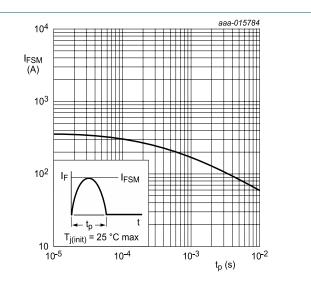


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig 5	-	-	6.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W

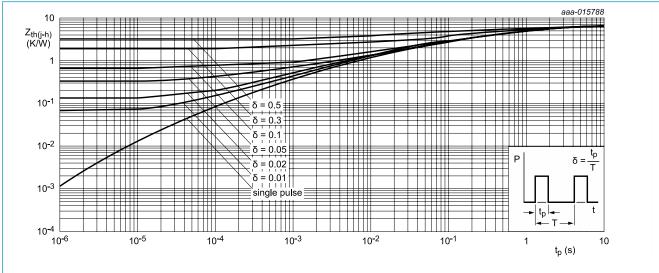


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

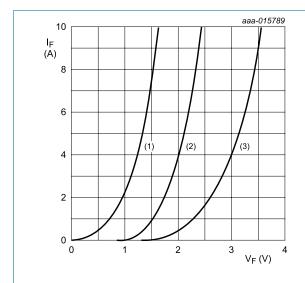
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all pins to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

11. Characteristics

Table 8 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	racteristics		I I			
V _F	forward voltage	I _F = 5 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.5	3.3	V
		I _F = 5 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.35	2.1	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	0.6	mA
Dynamic	characteristics					
Q_r	recovered charge	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	19	-	nC
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	45	-	nC
t _{rr} revers	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	11	-	ns
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	23	-	ns
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	28	-	ns
		$I_F = 5 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	13	25	ns
I _{RM}	peak reverse recovery current	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	1.7	-	А
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_i = 125 \text{ °C}; Fig. 7$	-	3.2	-	А



 $V_o = 1.833 \text{ V}; R_s = 0.055 \Omega$

(1) $T_i = 150 \,^{\circ}\text{C}$; typical values

(2) $T_j = 150$ °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

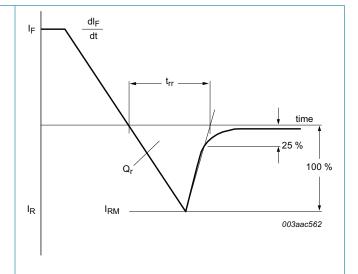
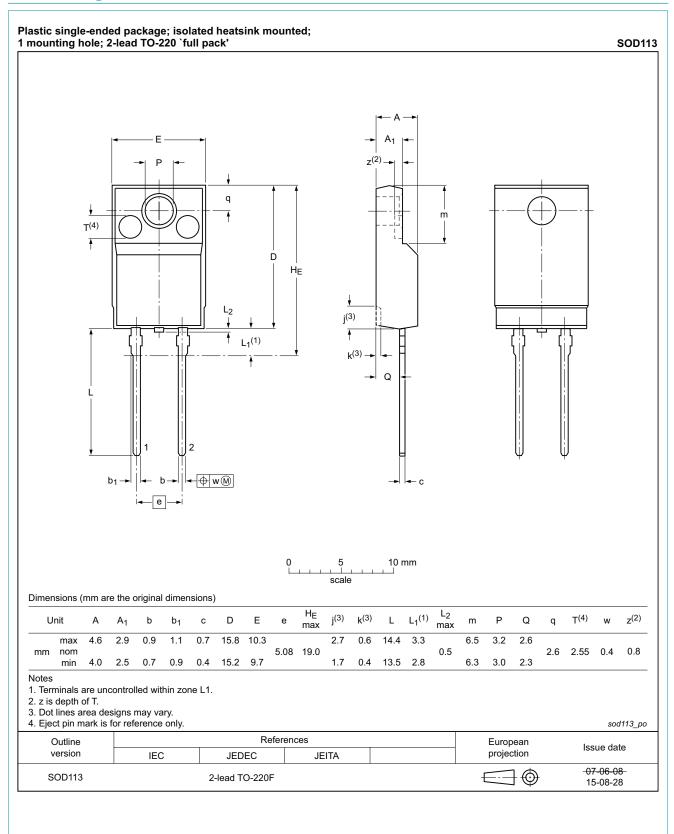


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline



13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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